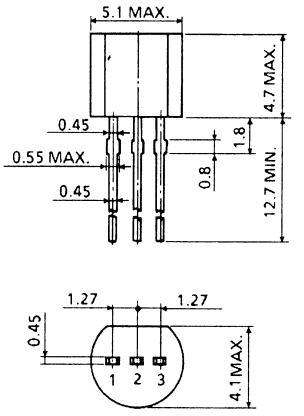
TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA970

LOW NOISE AUDIO AMPLIFIER APPLICATIONS

Unit in mm

- Low Noise
  : NF = 3dB (Typ.) $R_G = 100\Omega$, $V_{CE} = -6V$, $I_C = -100\mu A$, f = 1kHz
  : NF = 0.5dB (Typ.) $R_G = 1k\Omega$, $V_{CE} = -6V$, $I_C = -100\mu A$, f = 1kHz
- High DC Current Gain : $h_{FE} = 200 \sim 700$
- High Breakdown Voltage : $V_{CEO} = -120V$
- Low Pulse Noise. Low 1/f Noise



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1B

Weight : 0.21g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−120	V
Collector-Emitter Voltage	V_{CEO}	−120	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−100	mA
Base Current	I_B	−20	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V$, $I_E = 0$	—	—	−0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V$, $I_C = 0$	—	—	−0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA$, $I_B = 0$	−120	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -6V$, $I_C = -2mA$	200	—	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA$, $I_B = -1mA$	—	—	−0.3	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -6V$, $I_C = -2mA$	—	0.65	—	V
Transition Frequency	f_T	$V_{CE} = -6V$, $I_C = -1mA$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V$, $I_E = 0$, f = 1MHz	—	4.0	—	pF
Noise Figure	NF	$V_{CE} = -6V$, $I_C = -0.1mA$, f = 10Hz, $R_G = 10k\Omega$	—	—	6	dB
		$V_{CE} = -6V$, $I_C = -0.1mA$, f = 1kHz, $R_G = 10k\Omega$	—	—	2	
		$V_{CE} = -6V$, $I_C = -0.1mA$, f = 1kHz, $R_G = 100\Omega$	—	3	—	

Note : h_{FE} Classification GR : 200~400, BL : 350~700

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